

IN THE SPECIFICATION

Please replace the paragraph at page 1, lines 17-20, with the following rewritten paragraph:

In particular, in the case of optically coupling an optical fiber to an optical semiconductor element such as a semiconductor laser element (LD) or a waveguide-type photodiode (WG-PD), the alignment precision must be controlled within  $[[K]] \pm 1 \mu\text{m}$  or so.

Please replace the paragraph at page 3, lines 3-12, with the following rewritten paragraph:

This is because the top surface of the optical semiconductor element, which was formed through vapor phase epitaxial growth technique, is superior in the preciseness of thickness of each semiconductor layer, typically being controlled within  $[[K]] \pm 0.1 \mu\text{m}$  or so, to the bottom surface which generally has a roughness in the range of  $[[K]] \pm 10 \mu\text{m}$  or so even after a polishing process. Hence, the top surface is more suitable than the bottom surface to be used as a reference plane above which the height of the active layer, or a light-emitting/light-receiving portion of the optical semiconductor element, is determined, helping to ensure the alignment precision in the direction perpendicular to a mounting surface of the mounting substrate.